PHP36N03LT

N-channel TrenchMOS logic level FET

Rev. 04 — 8 July 2010 — Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Simple gate drive required due to low gate charge
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

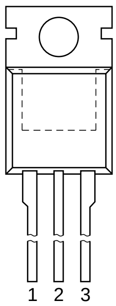
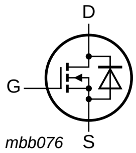
1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C	-	-	30	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1; see Figure 3	-	-	43.4	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	-	57.6	W
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 9; see Figure 10	-	14	17	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 36 A; V_{DS} = 15 V; T_j = 25 °C; see Figure 11; see Figure 12	-	2.9	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source[1]		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHP36N03LT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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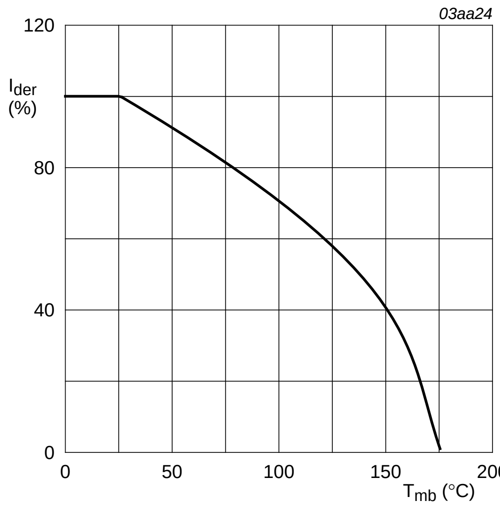
4. Limiting values

Table 4. Limiting values

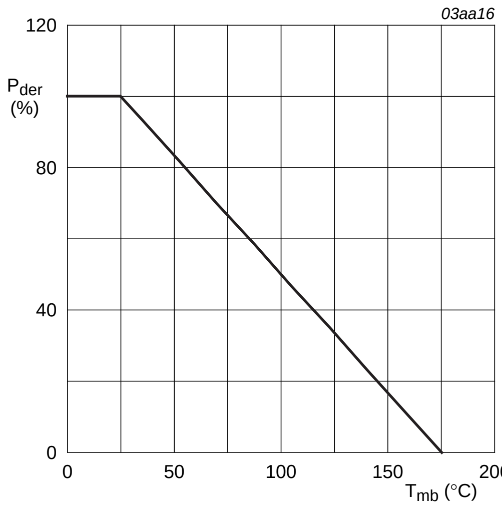
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	30	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 100$ °C; see Figure 1	-	30.7	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 1; see Figure 3	-	43.4	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; see Figure 3	-	173.6	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	57.6	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25$ °C	-	43.4	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C	-	173.6	A



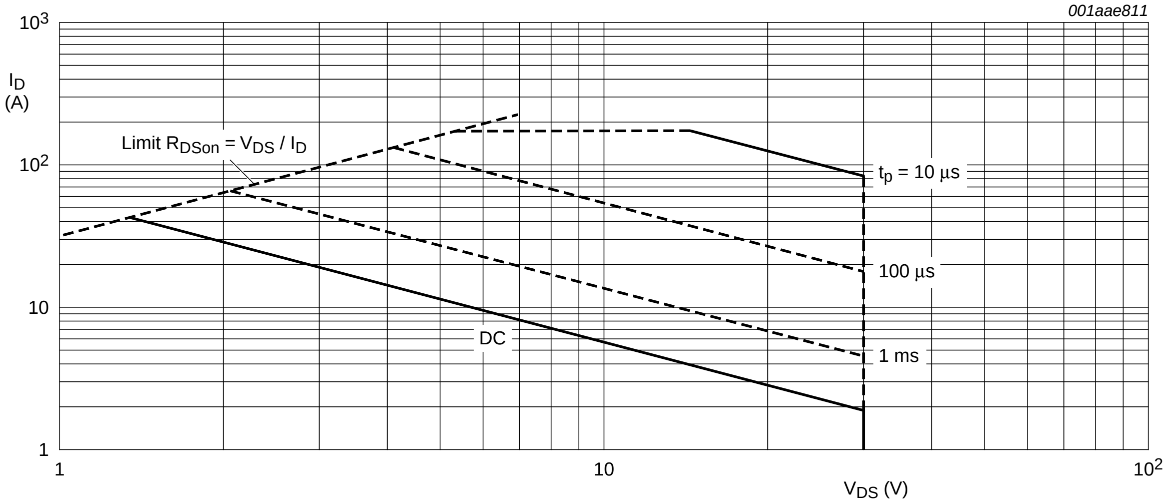
$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25\ °C; I_{DM}$ is single pulse; $V_{GS} = 10\ V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

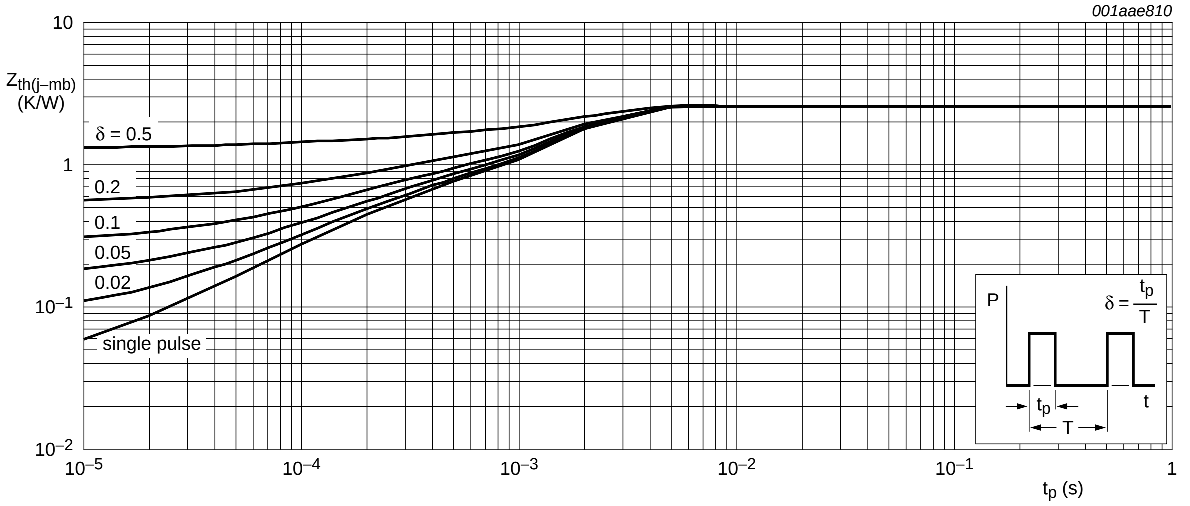
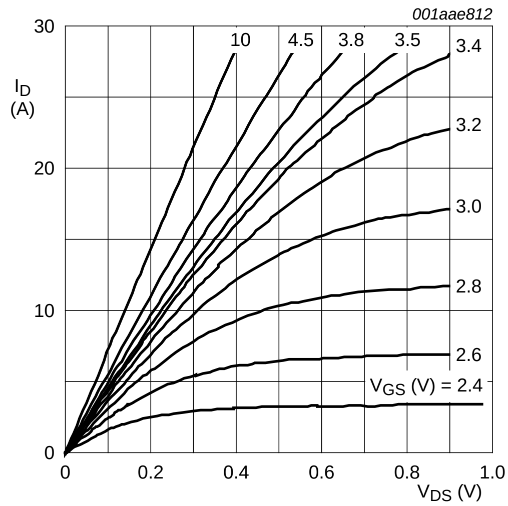


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

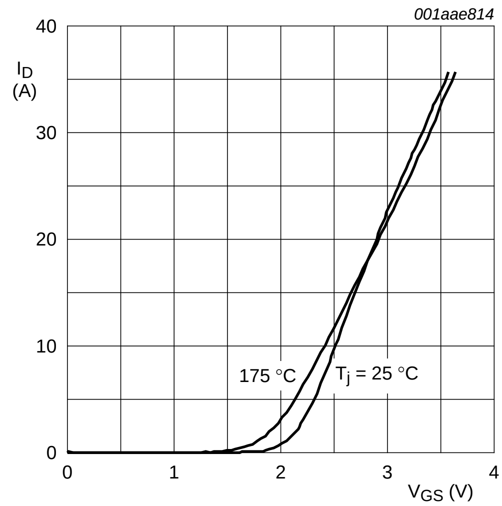
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 7; see Figure 8	0.5	-	-	V
		I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 7; see Figure 8	1	1.5	2	V
		I_D = 250 µA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 7; see Figure 8	-	-	2.2	V
I_{DSS}	drain leakage current	V_{DS} = 24 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	1	µA
		V_{DS} = 24 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 9; see Figure 10	-	14	17	mΩ
		V_{GS} = 4.5 V; I_D = 12 A; T_j = 175 °C; see Figure 9; see Figure 10	-	32.4	39.6	mΩ
		V_{GS} = 3.5 V; I_D = 5.2 A; T_j = 25 °C; see Figure 9; see Figure 10	-	22	40	mΩ
		V_{GS} = 4.5 V; I_D = 12 A; T_j = 25 °C; see Figure 9; see Figure 10	-	18	22	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 36 A; V_{DS} = 15 V; V_{GS} = 10 V; T_j = 25 °C; see Figure 11; see Figure 12	-	18.5	-	nC
Q_{GS}	gate-source charge		-	4.2	-	nC
Q_{GD}	gate-drain charge		-	2.9	-	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 13	-	690	-	pF
C_{oss}	output capacitance	V_{DS} = 0 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 13	-	160	-	pF
C_{rss}	reverse transfer capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 13	-	110	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; T_j = 25 °C	-	6	-	ns
t_r	rise time		-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	33	-	ns
t_f	fall time		-	19	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 14	-	0.97	1.2	V



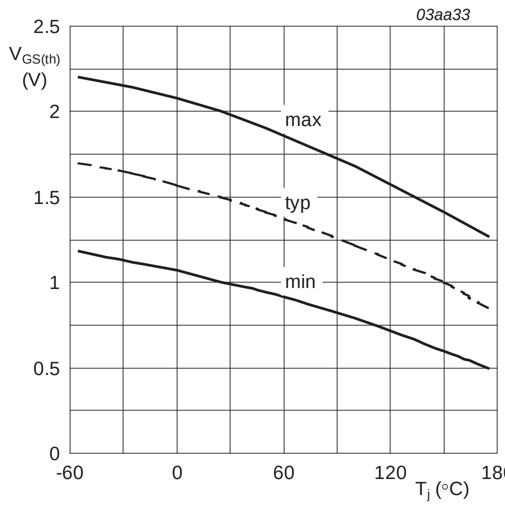
$T_j = 25\ °C$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



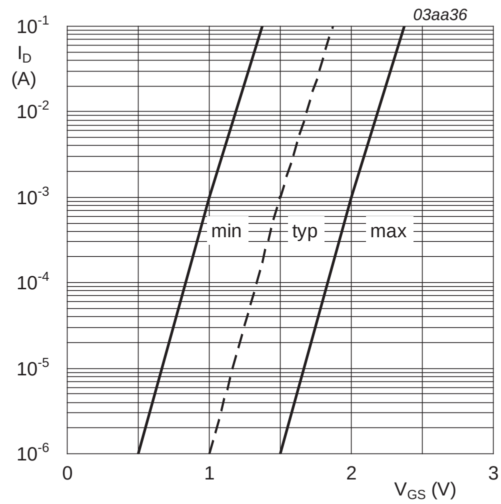
$V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



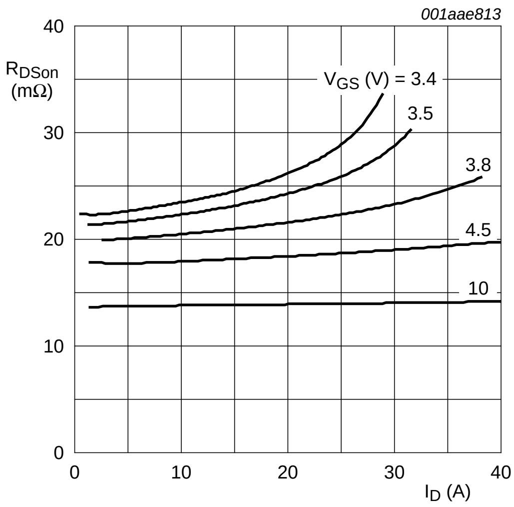
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 7. Gate-source threshold voltage as a function of junction temperature



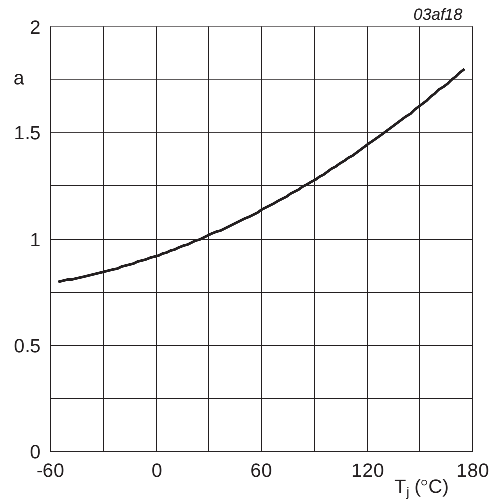
$T_j = 25\,°C; V_{DS} = V_{GS}$

Fig 8. Sub-threshold drain current as a function of gate-source voltage



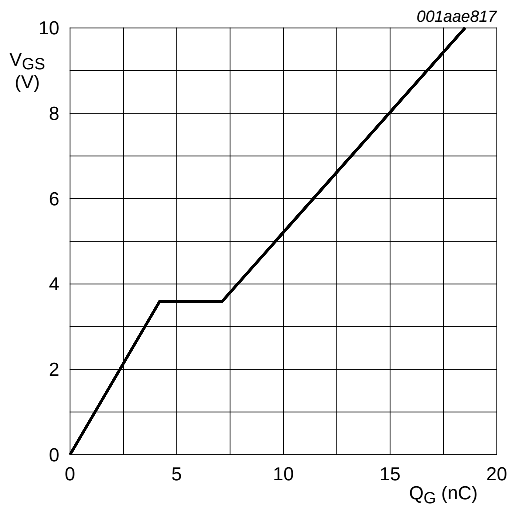
$T_j = 25\ °C$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



$I_D = 36\ A; V_{DS} = 15\ V$

Fig 11. Gate-source voltage as a function of gate charge; typical values

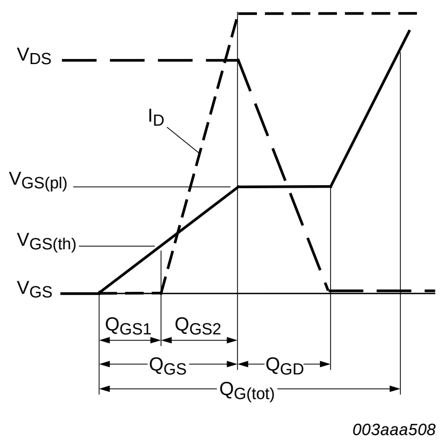
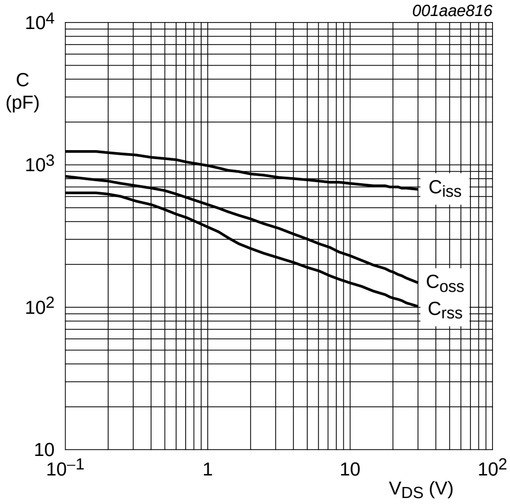
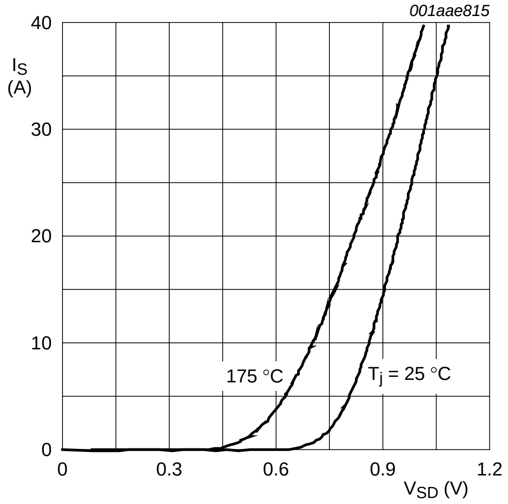


Fig 12. Gate charge waveform definitions



$V_{GS} = 0\ V; f = 1\ MHz$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

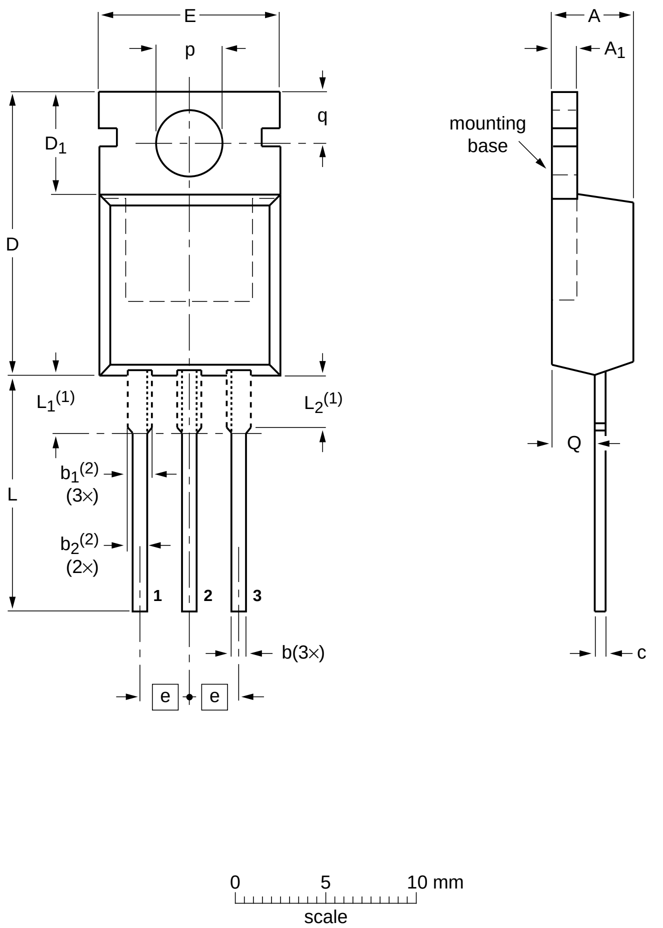


$V_{GS} = 0\ V$

Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	$b_1^{(2)}$	$b_2^{(2)}$	c	D	D_1	E	e	L	$L_1^{(1)}$	$L_2^{(1)}$ max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

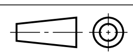
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig 15. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP36N03LT v.4	20100708	Product data sheet	-	PHP36N03LT v.3
Modifications:	• Various changes to content.			
PHP36N03LT v.3	20100329	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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11. Contents

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